

**8A, 1200V Ultrafast Dual Diode**

The RURP8120CC is an ultrafast dual diode with soft recovery characteristics ( $t_{rr} < 100ns$ ). It has low forward voltage drop and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast soft recovery minimizes ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

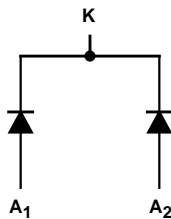
Formerly development type TA49095.

**Ordering Information**

PART NUMBER	PACKAGE	BRAND
RURP8120CC	TO-220AB	RUR8120C

NOTE: When ordering, use the entire part number.

**Symbol**



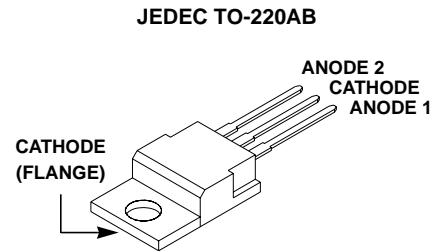
**Features**

- Ultrafast with Soft Recovery . . . . . <100ns
- Operating Temperature . . . . . 175°C
- Reverse Voltage . . . . . 1200V
- Avalanche Energy Rated
- Planar Construction

**Applications**

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

**Packaging**



**Absolute Maximum Ratings** (Per Leg)  $T_C = 25^{\circ}C$ , Unless Otherwise Specified

	RURP8120CC	UNITS
Peak Repetitive Reverse Voltage . . . . . $V_{RRM}$	1200	V
Working Peak Reverse Voltage . . . . . $V_{RWM}$	1200	V
DC Blocking Voltage . . . . . $V_R$	1200	V
Average Rectified Forward Current . . . . . $I_{F(AV)}$ ( $T_C = 144^{\circ}C$ )	8	A
Repetitive Peak Surge Current . . . . . $I_{FRM}$ (Square Wave, 20kHz)	16	A
Nonrepetitive Peak Surge Current . . . . . $I_{FSM}$ (Halfwave, 1 Phase, 60Hz)	100	A
Maximum Power Dissipation . . . . . $P_D$	75	W
Avalanche Energy (See Figure 10 and Figure 11) . . . . . $E_{AVL}$	20	mJ
Operating and Storage Temperature . . . . . $T_{STG}, T_J$	-65 to 175	°C

**Electrical Specifications** (Per Leg)  $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
$V_F$	$I_F = 8\text{A}$	-	-	2.1	V
	$I_F = 8\text{A}, T_C = 150^\circ\text{C}$	-	-	1.9	V
$I_R$	$V_R = 1200\text{V}$	-	-	100	$\mu\text{A}$
	$V_R = 1200\text{V}, T_C = 150^\circ\text{C}$	-	-	500	$\mu\text{A}$
$t_{rr}$	$I_F = 1\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	100	ns
	$I_F = 8\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	110	ns
$t_a$	$I_F = 8\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	60	-	ns
$t_b$	$I_F = 8\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	40	-	ns
$Q_{RR}$	$I_F = 8\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	380	-	nC
$C_J$	$V_R = 10\text{V}, I_F = 0\text{A}$	-	25	-	pF
$R_{\theta JC}$		-	-	2	$^\circ\text{C}/\text{W}$

DEFINITIONS

$V_F$  = Instantaneous forward voltage (pw = 300 $\mu\text{s}$ , D = 2%).

$I_R$  = Instantaneous reverse current.

$t_{rr}$  = Reverse recovery time (See Figure 9), summation of  $t_a + t_b$ .

$t_a$  = Time to reach peak reverse current (See Figure 9).

$t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 9).

$R_{\theta JC}$  = Thermal resistance junction to case.

$Q_{RR}$  = Reverse Recovery Charge.

$C_J$  = Junction Capacitance.

pw = pulse width.

D = duty cycle.

**Typical Performance Curves**

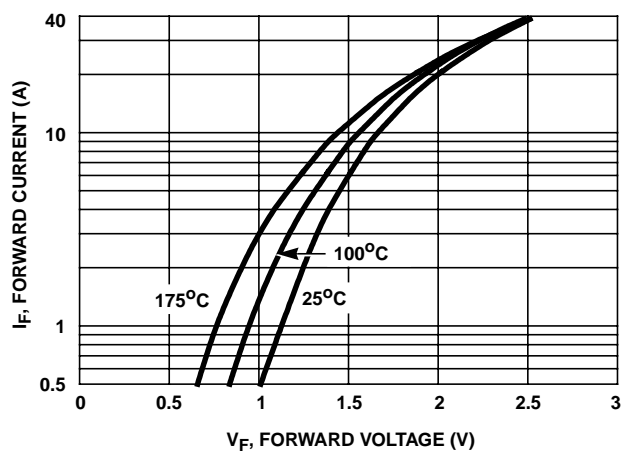


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

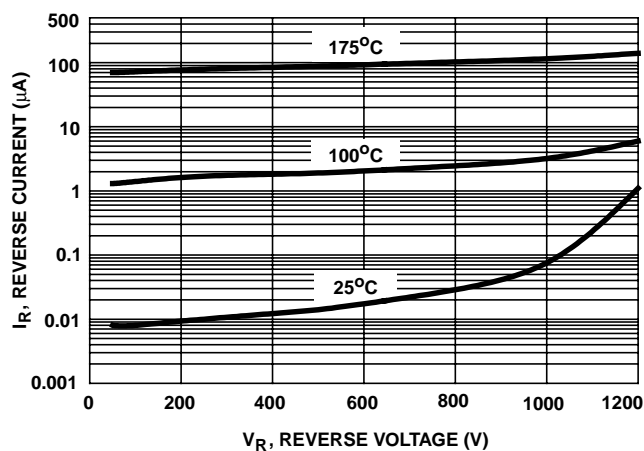


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

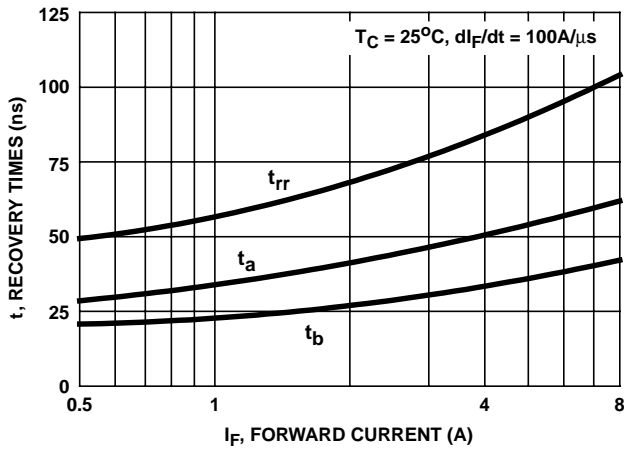


FIGURE 3.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

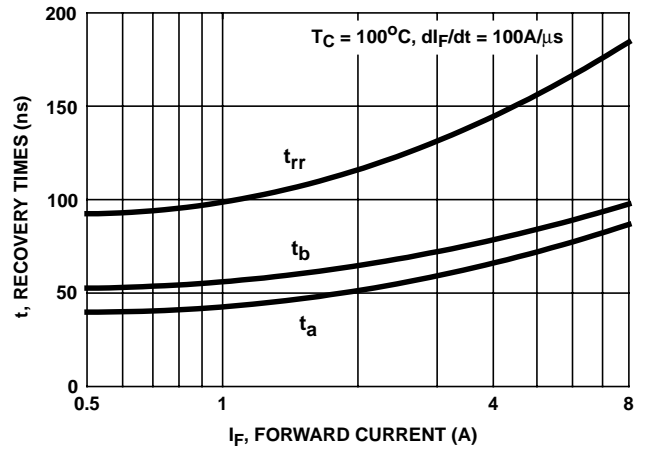


FIGURE 4.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

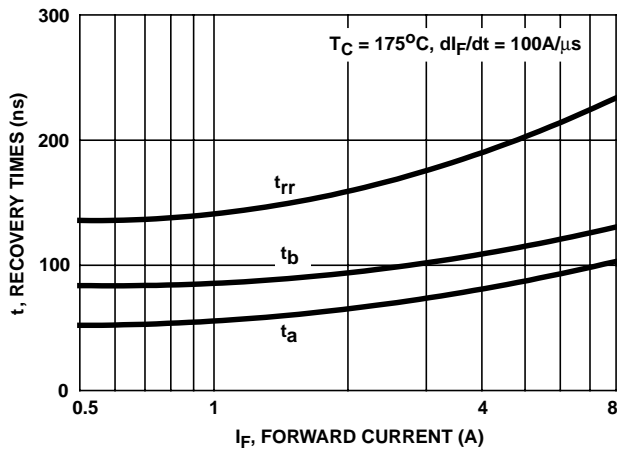


FIGURE 5.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

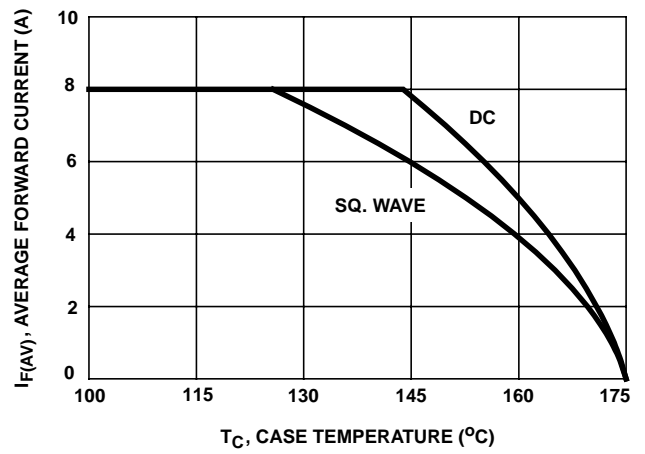


FIGURE 6. CURRENT DERATING CURVE

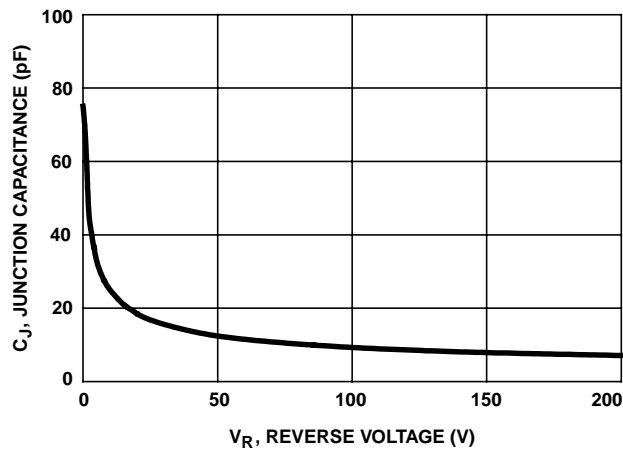


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

**Test Circuits and Waveforms**

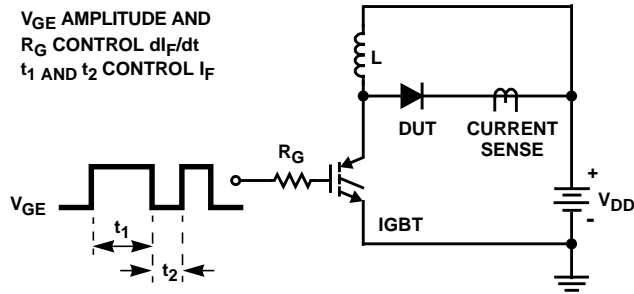


FIGURE 8.  $t_{rr}$  TEST CIRCUIT

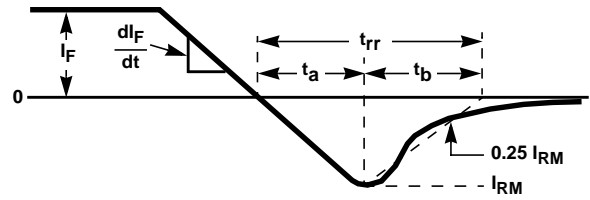


FIGURE 9.  $t_{rr}$  WAVEFORMS AND DEFINITIONS

$I = 1A$   
 $L = 40mH$   
 $R < 0.1\Omega$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$   
 $Q_1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

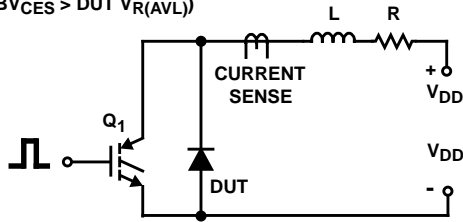


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

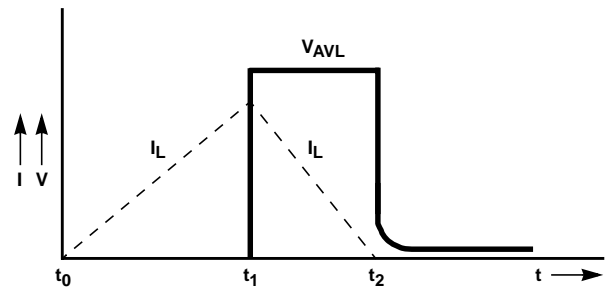


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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